

Schottky Diodes

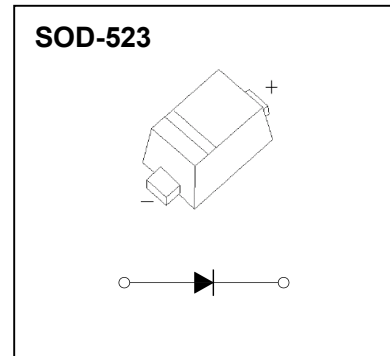
1SS389

FEATURES

- High Speed
- High Reliability
- Small Package
- Low Forward Voltage

APPLICATIONS

- High Speed Switching

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_R	DC Blocking Voltage	10	V
I_O	Continuous Forward Current	100	mA
I_{FM}	Peak Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @10ms	1	A
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	667	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	10			V
Reverse current	I_R	$V_R=10\text{V}$			20	μA
Forward voltage	V_F	$I_F=1\text{mA}$		0.18		V
		$I_F=5\text{mA}$			0.3	
		$I_F=100\text{mA}$			0.5	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			40	pF

■ Marking

Marking	S4
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